

MOS INTEGRATED CIRCUIT μ PD16813

MONOLITHIC DUAL H BRIDGE DRIVER CIRCUIT

DESCRIPTION

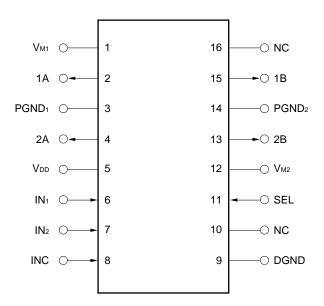
The μ PD16813 is a monolithic dual H bridge driver circuit which uses power MOS FETs in its driver stage. By complementing the P channel and N channel of the output stage, the circuit current has been substantially inproved as compared with that of conventional charge pump drivers.

The μ PD16813 is therefore ideal as the driver circuit of the 2-phase excitation, bipolar-driven stepping motor for the head actuator of an FDD.

FEATURES

- Low ON resistance (sum of ON resistors of top and bottom transistors) Ron = 2.0Ω TYP.
- Low current consumption: IDD = 100 μ A MAX.
- · Noise reduction circuit that operates when INC is OFF.
- Compact surface mount package: 16-pin plastic SOP (300 mil)

PIN CONFIGURATION (Top View)

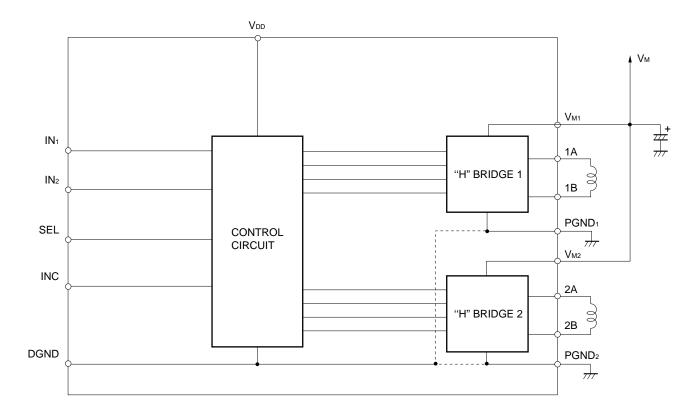


ORDERING INFORMATION

Part Number	Package
μPD16813GS	16-pin plastic SOP (300 mil)



BLOCK DIAGRAM



FUNCTION TABLE

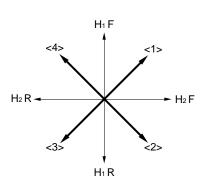
• In stop mode (SEL = High)

Excitation Direction	INC	IN ₁	IN ₂	H ₁	H ₂
<1>	Н	Н	Н	F	F
<2>	Н	L	Н	R	F
<3>	Н	L	L	R	R
<4>	Н	Н	L	F R	
_	L	×	×	Stop	

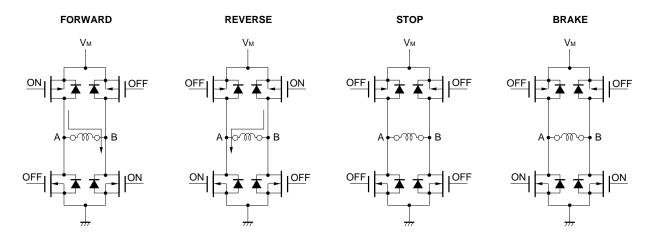
• In brake mode (SEL = Low)

Excitation Direction	INC	IN ₁	IN ₂	H₁	H ₂
<1>	Н	Н	Н	F	F
<2>	Н	L	Н	R	F
<3>	Н	L	L	R	R
<4>	Н	Н	L	F	R
-	L	×	×	Brake	

F: Forward
R: Reverse
x: Don't care





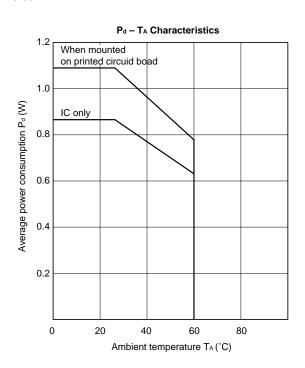


ABSOLUTE MAXIMUM RATINGS (TA = +25 °C)

Parameter	Symbol	Rating	Unit
Supply voltage (motor block)	Vм	-0.5 to +7	V
Supply voltage (control block)	V _{DD}	-0.5 to +7	V
Power consumption	P _{d1}	0.862 ^{Note 1}	W
	P _{d2}	1.087 ^{Note 2}	
Instantaneous H bridge driver current	I□ (pulse)	±1.0Note 2, 3	А
Input voltage	Vin	-0.5 to V _{DD} + 0.5	V
Operating temperature range	TA	0 to 60	°C
Operation junction temperature	Тј мах.	150	°C
Storage temperature range	T _{stg}	-55 to +125	°C

Notes 1. IC only

- 2. When mounted on a printed circuit board ($100 \times 100 \times 1$ mm, glass epoxy)
- **3.** $t \le 5$ ms, Duty ≤ 40 %





RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage (motor block)	Vм	4.0	5.0	6.0	٧
Supply voltage (control block)	V _{DD}	4.0	5.0	6.0	V
H bridge driver current ^{Note}	Idr			±310	mA
Operating temperature	TA	0		60	°C

Note When mounted on a printed circuit board $(100 \times 100 \times 1 \text{ mm}, \text{ glass epoxy})$

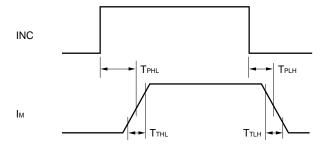
ELECTRICAL SPECIFICATIONS (Within recommended operating conditions unless otherwise specified)

Parameters	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V _M pin current	Ім	VM = 6.0 V, VDD = 6.0 V			1.0	μΑ
V _{DD} pin current	IDD				0.1	mA
Control pin high-level input current	Іін	VIN = VDD			1.0	μΑ
Control pin low-level input current	lı∟	Vin = 0 V			-1.0	μΑ
Control pin high-level input voltage	ViH		3.0		V _{DD} + 0.3	V
Control pin low-level input voltage	VIL		-0.3		0.8	V
H bridge circuit ON resistanceNote 1	Ron1	V _M = 5 V, V _{DD} = 5 V		2.0	4.0	Ω
Ron relative accuracy	ΔR on	Excitation direction <2>, <4>Note 2			±5	%
	ΔRon	Excitation direction <1>, <3>			±10	
H bridge circuit propagation delay time	t PHL	$V_{M} = 5 \text{ V}, V_{DD} = 5 \text{ V}, \text{Note 3}$ $T_{A} = 25 \text{ °C}, R_{M} = 20 \Omega$		2.0	2.5	μs
H bridge circuit propagation delay time	tрын			0.4	0.65	μs
H bridge circuit rise time	t⊤н∟	V _M = 5 V, V _{DD} = 5 V, Note 3		0.2	0.4	μs
H bridge circuit fall time	tтьн	$T_A = 25$ °C, $R_M = 20 \Omega$		0.1	0.2	μs

Notes 1. Sum of ON resistances of top and bottom transistors

2. For the excitation direction, refer to FUNCTION TABLE.

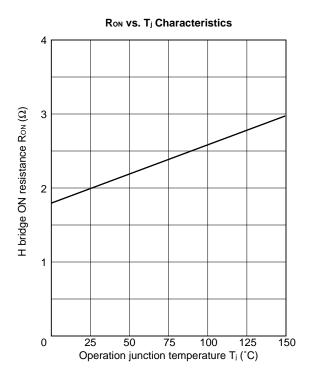
3.

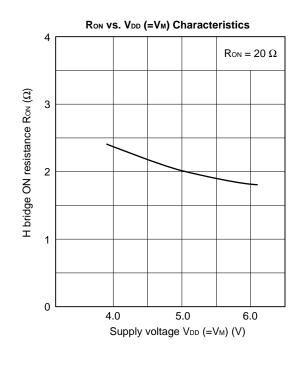


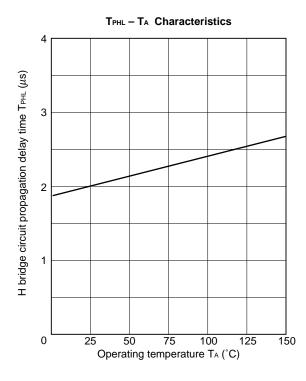
4

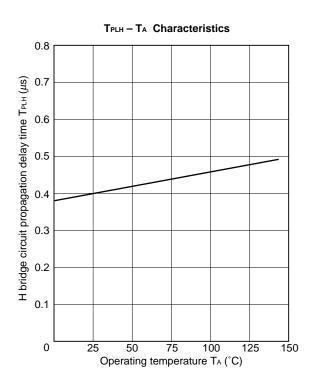


CHARACTERISTIC CURVES

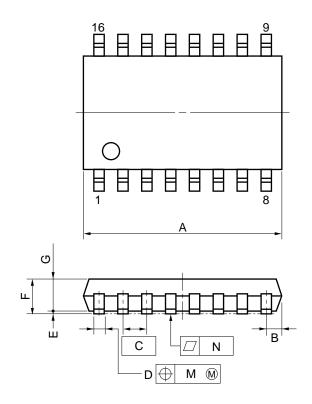




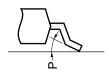


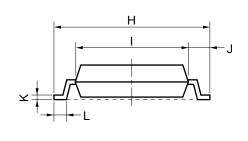


16 PIN PLASTIC SOP (300 mil)



detail of lead end





NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
Α	10.46 MAX.	0.412 MAX.
В	0.78 MAX.	0.031 MAX.
С	1.27 (T.P.)	0.050 (T.P.)
D	$0.40^{+0.10}_{-0.05}$	$0.016^{+0.004}_{-0.003}$
E	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.55	0.061
Н	7.7±0.3	0.303±0.012
I	5.6	0.220
J	1.1	0.043
K	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$
L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
М	0.12	0.005
N	0.10	0.004
Р	3°+7° -3°	3°+7°

P16GM-50-300B-4



RECOMMENDED SOLDERING CONDITIONS

It is recommended to solder this product under the conditions described below. For soldering methods and conditions other than those listed below, consult NEC.

Surface mount type

For the details of the recommended soldering conditions of this type, refer to **Semiconductor Device Mounting Technology Manual (C10535E)**.

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering
Infrared reflow	Peak package temperature: 230 °C, Time: 30 seconds MAX. (210 °C MIN.), Number of times: 1, Number of days: None ^{Note}	IR30-00
VPS	Peak package temperature: 215 °C, Time: 40 seconds MAX. (200 °C MIN.), Number of times: 1, Number of days: None ^{Note}	VP15-00
Wave soldering	Solder bath temperature: 260 °C MAX., Time: 10 seconds MAX., Number of times: 1, Number of days: None ^{Note}	WS60-00
Partial heating	Pin temperature: 300 °C MAX., Time: 10 seconds MAX., Number of days: None ^{Note}	-

Note The number of storage days at 25 °C, 65 % RH after the dry pack has been opened

Caution Do not use two or more soldering methods in combination (except partial heating).

7

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.

M4 96.5